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[Continued on next page]

(54) Title: ANTI-FUSE MEMORY CELL

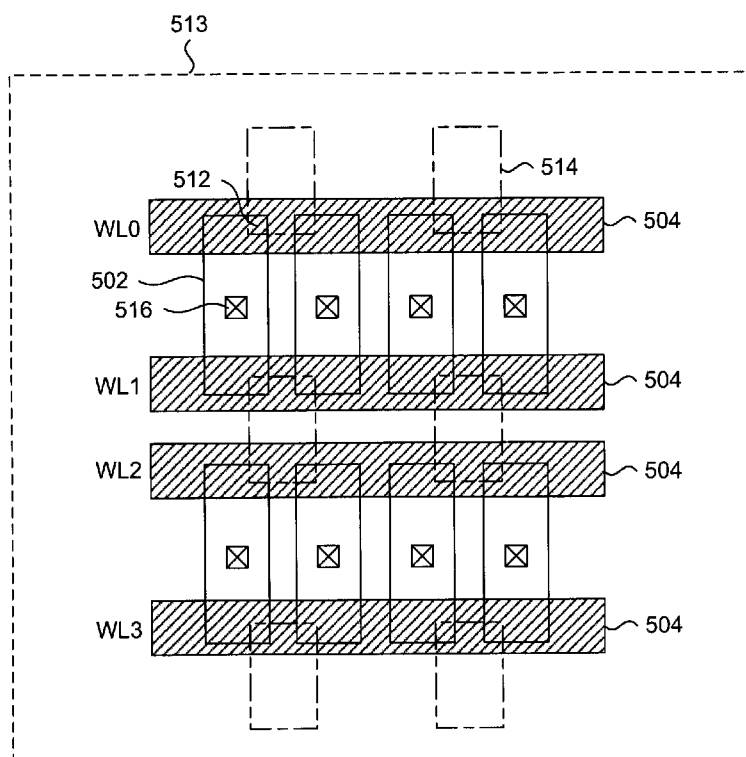


Figure 10

(57) Abstract: An anti-fuse memory cell having a variable thickness gate oxide. The variable thickness gate oxide has a thick gate oxide portion and a thin gate oxide portion, where the thin gate oxide portion has at least one dimension less than a minimum feature size of a process technology. The thin gate oxide can be rectangular in shape or triangular in shape. The anti-fuse transistor can be used in a two-transistor memory cell having an access transistor with a gate oxide substantially identical in thickness to the thick gate oxide of the variable thickness gate oxide of the anti-fuse transistor.



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